

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

KEY PARAMETERS

V_{DRM}	1800V
$I_{T(AV)}$	720A
I_{TSM}	8300A
dV/dt^*	1000V/μs
dI/dt	200A/μs

* Higher dV/dt selections are available

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} (V)	Conditions
DCR720E18	1800	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 30\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR720E16	1600	
DCR720E14	1400	
DCR720E12	1200	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR720E18

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

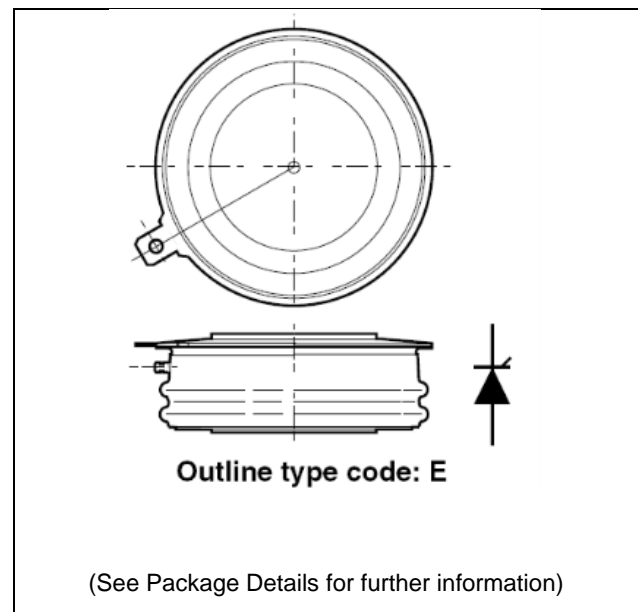


Fig. 1 Package outline

CURRENT RATINGS $T_{case} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	720	A
$I_{T(RMS)}$	RMS value	-	1230	A
I_r	Continuous (direct) on-state current	-	970	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{rSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	8.3	kA
I^2t	I^2t for fusing	$V_R = 0$	0.344	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled DC	-	0.041	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Double side cooled DC	-	0.01	$^{\circ}\text{C}/\text{W}$
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		-40	140	$^{\circ}\text{C}$
F_m	Clamping force		4	6	kN

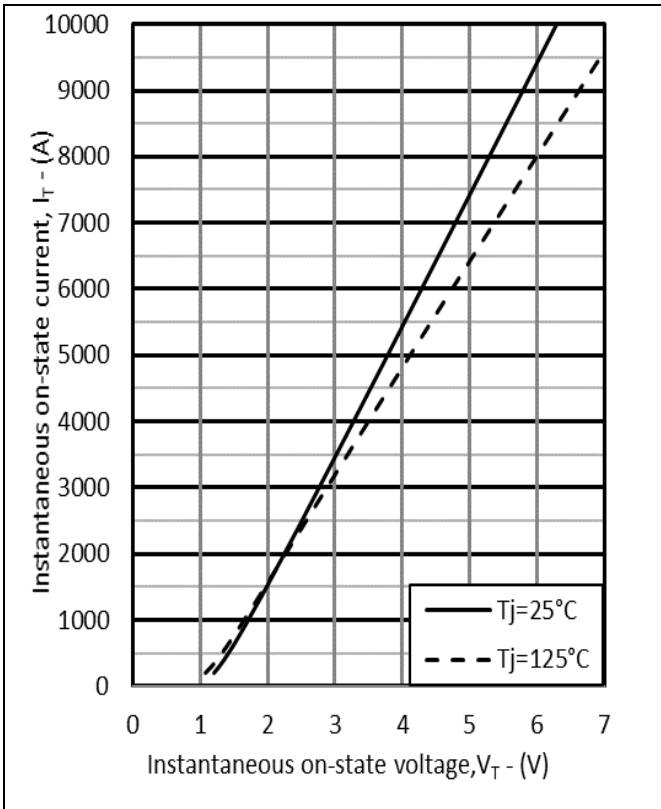
DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	30	mA	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	-	1000	V/ μ s	
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A	Repetitive	-	200	A/ μ s
		Gate source 30V, 10 Ω $t_r < 0.5\mu$ s, $T_j = 125^{\circ}C$	Non-repetitive	-	1000	A/ μ s
V_T	On-state voltage	$I_T = 1500A$, $T_{case} = 125^{\circ}C$		1.97	V	
$V_{T(RO)}$	Threshold voltage	$T_{case} = 125^{\circ}C$	-	1.09	V	
r_r	On-state slope resistance	$T_{case} = 125^{\circ}C$	-	0.587	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	-	3	μ s	
t_q	Turn-off time	$T_j = 125^{\circ}C$, $V_R = 100V$, $dI/dt = 10A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s linear to 67% V_{DRM}	-	150	μ s	
Q_s	Stored charge	$I_T = 1000A$, $T_j = 125^{\circ}C$, $dI/dt = 10A/\mu$ s, $t_p = 1000\mu$ s	-	1500	μ C	
I_{RR}	Reverse recovery current		-	110	A	
I_L	Latching current	$T_j = 25^{\circ}C$	-	1	A	
I_H	Holding current	$T_j = 25^{\circ}C$	-	200	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3	V
V_{GD}	Gate non-trigger voltage	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	0.3	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
I_{GD}	Gate non-trigger current	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	20	mA

CURVES



V_{TM} EQUATION

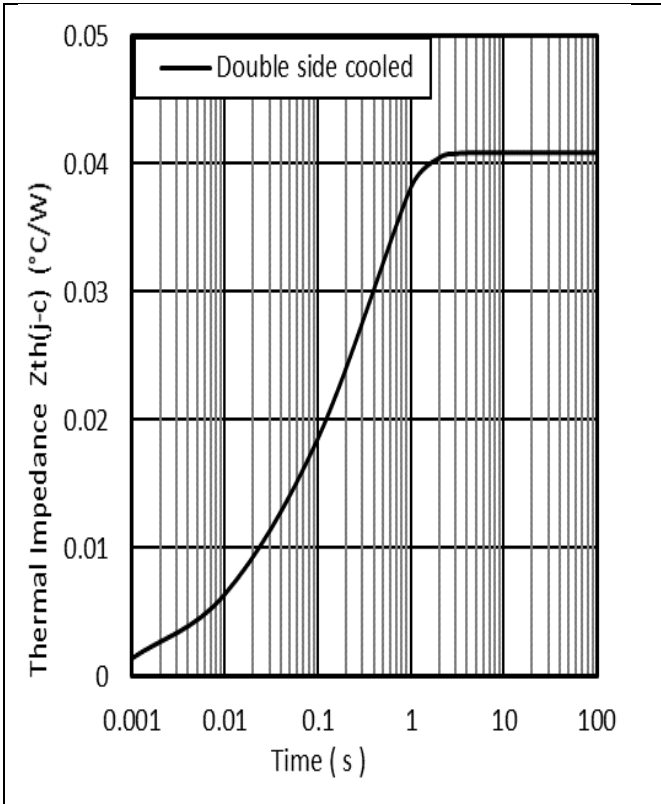
$$V_{TM} = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

- A = 0.213846
- B = 0.177258
- C = 0.000692251
- D = -0.0152068

These values are valid for T_j = 125°C

Fig. 2 Maximum on state characteristics



$$R_{thjc}(t) = \sum_{i=1}^n R_{thi} \cdot \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

i	τ _i (s)	R _{thi} (°C/kW)
1	0.5391689	16.5
2	0.1940576	14.19235
3	0.0219527	7.412673
4	0.0021962	2.759765

Fig. 3 Maximum (limit) transient thermal impedance - junction to case (°C/W)

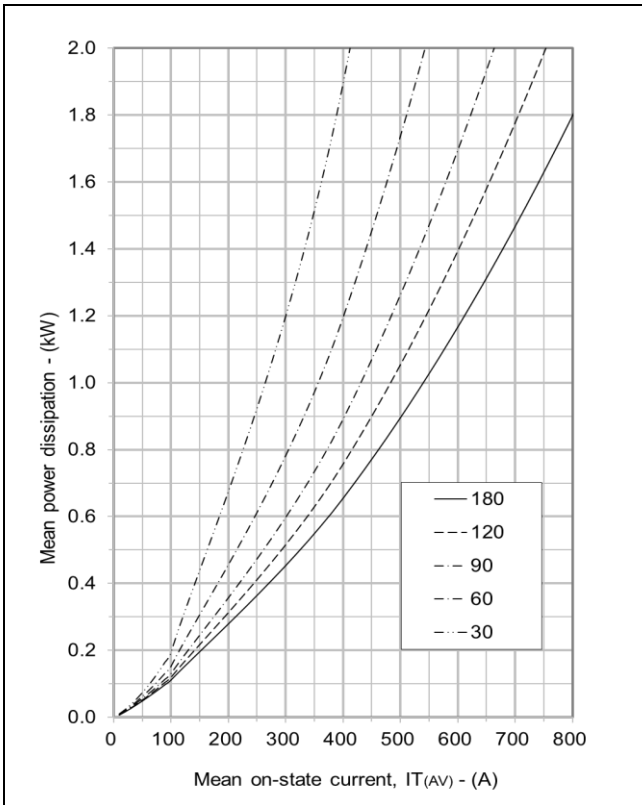


Fig. 4 On-state power dissipation - sine wave

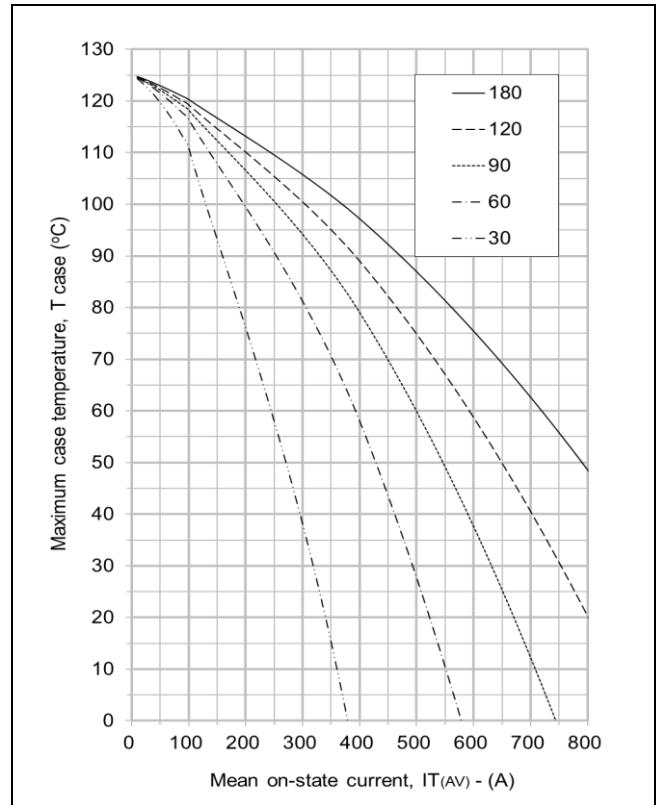


Fig. 5 Maximum permissible case temperature, double side cooled - sine wave

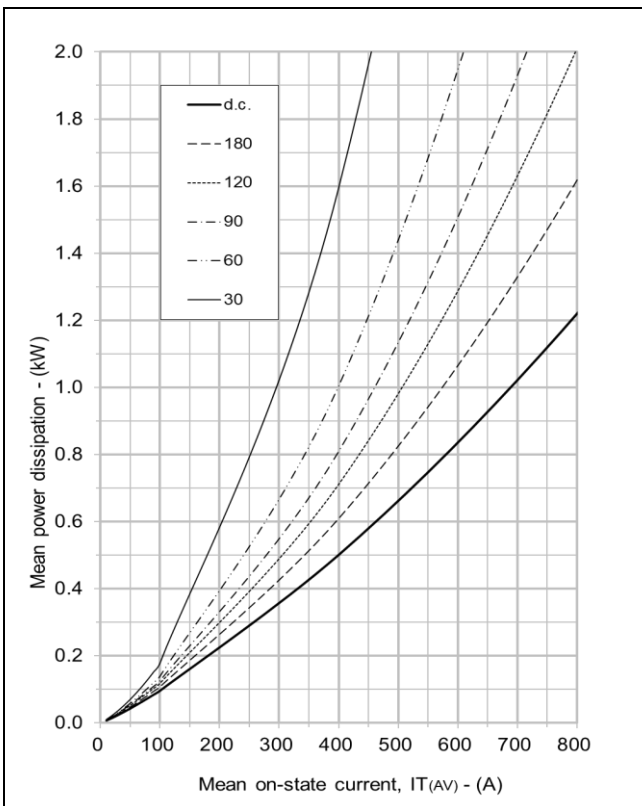


Fig. 6 On-state power dissipation - rectangular wave

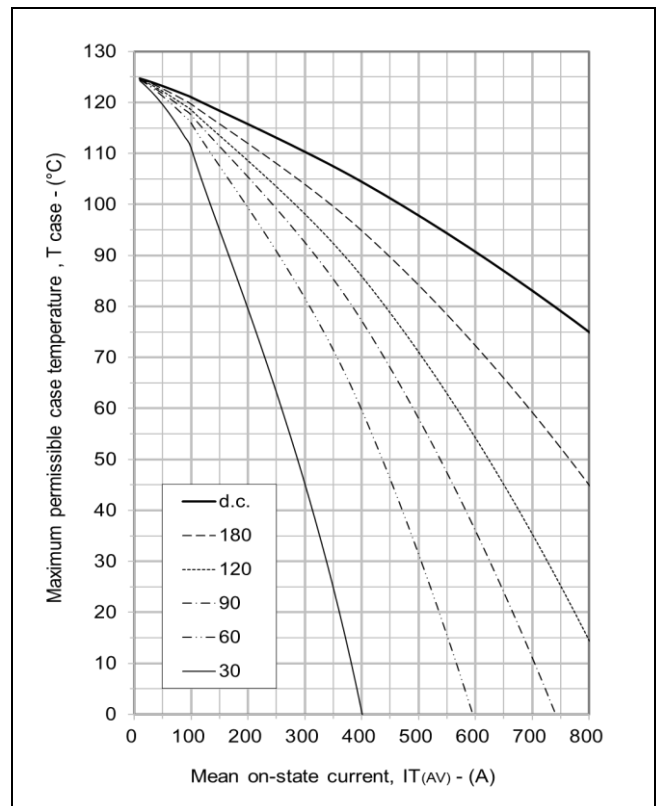


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave

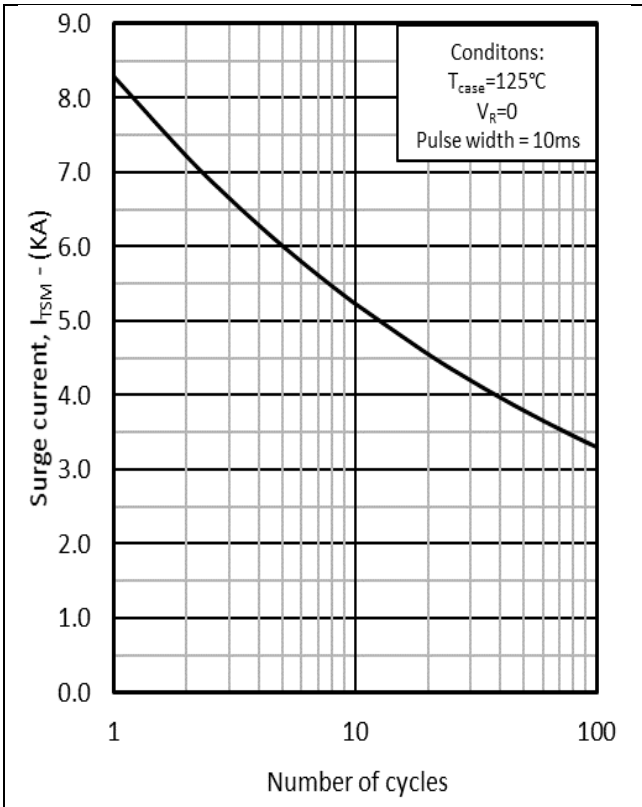


Fig. 8 Multi-cycle surge current

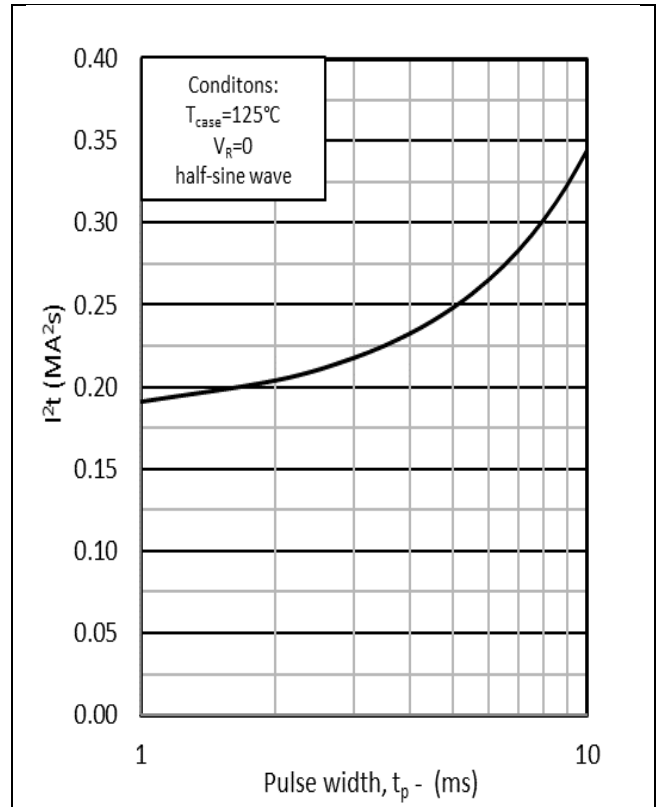


Fig. 9 Single-cycle I^2t

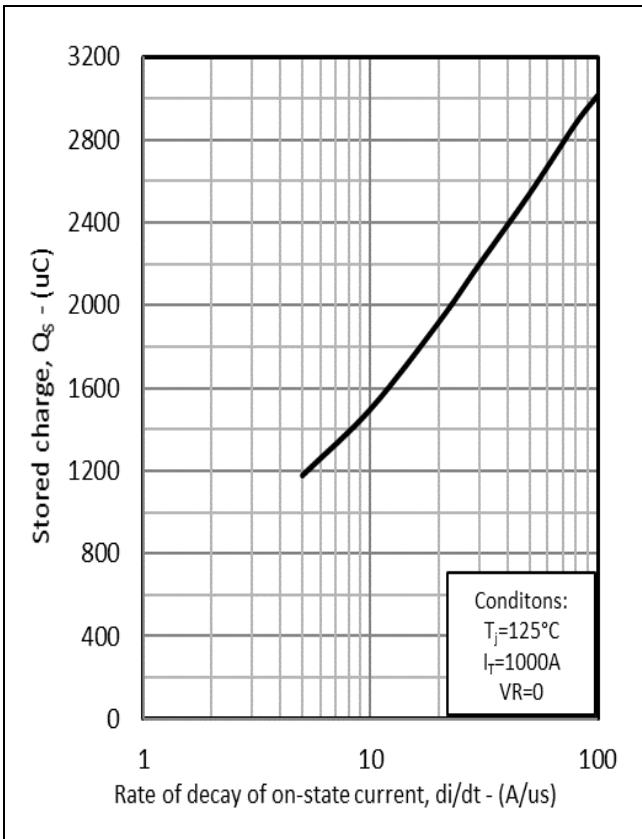


Fig. 10 Reverse recovery charge

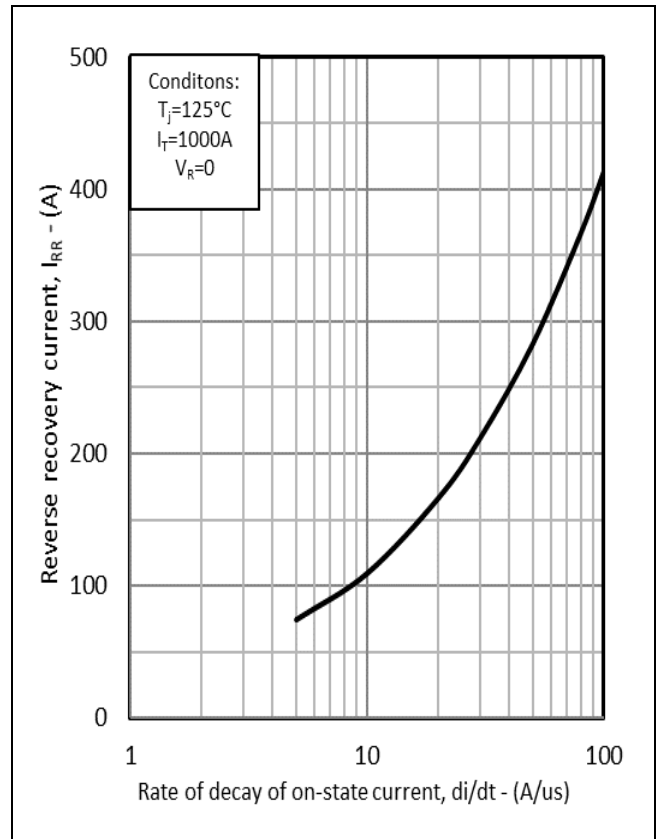


Fig. 11 Reverse recovery current

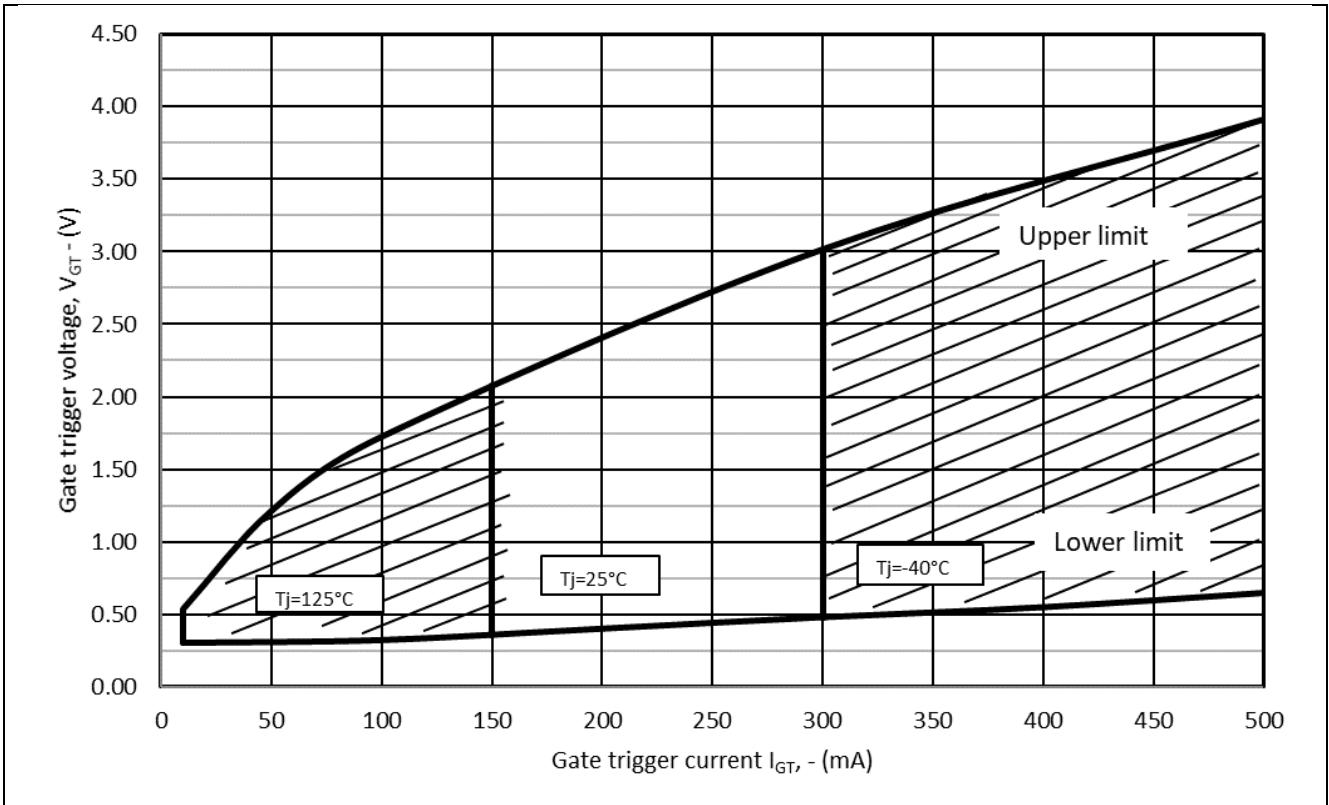
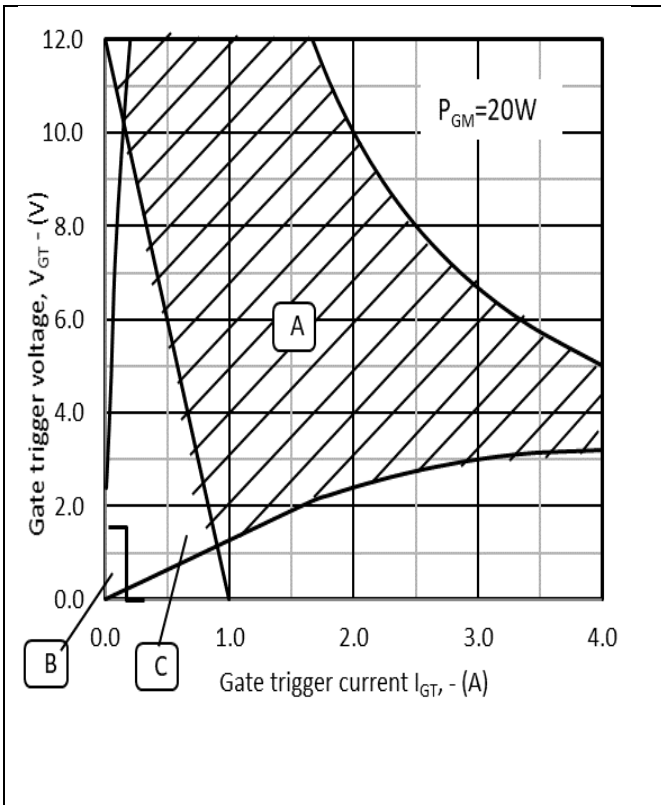


Fig. 12 Gate characteristics



- A: is Recommended Triggering Area.
- B: is Unreliable Triggering Area.
- C: is Recommended Gate Load Line.

Fig. 13 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

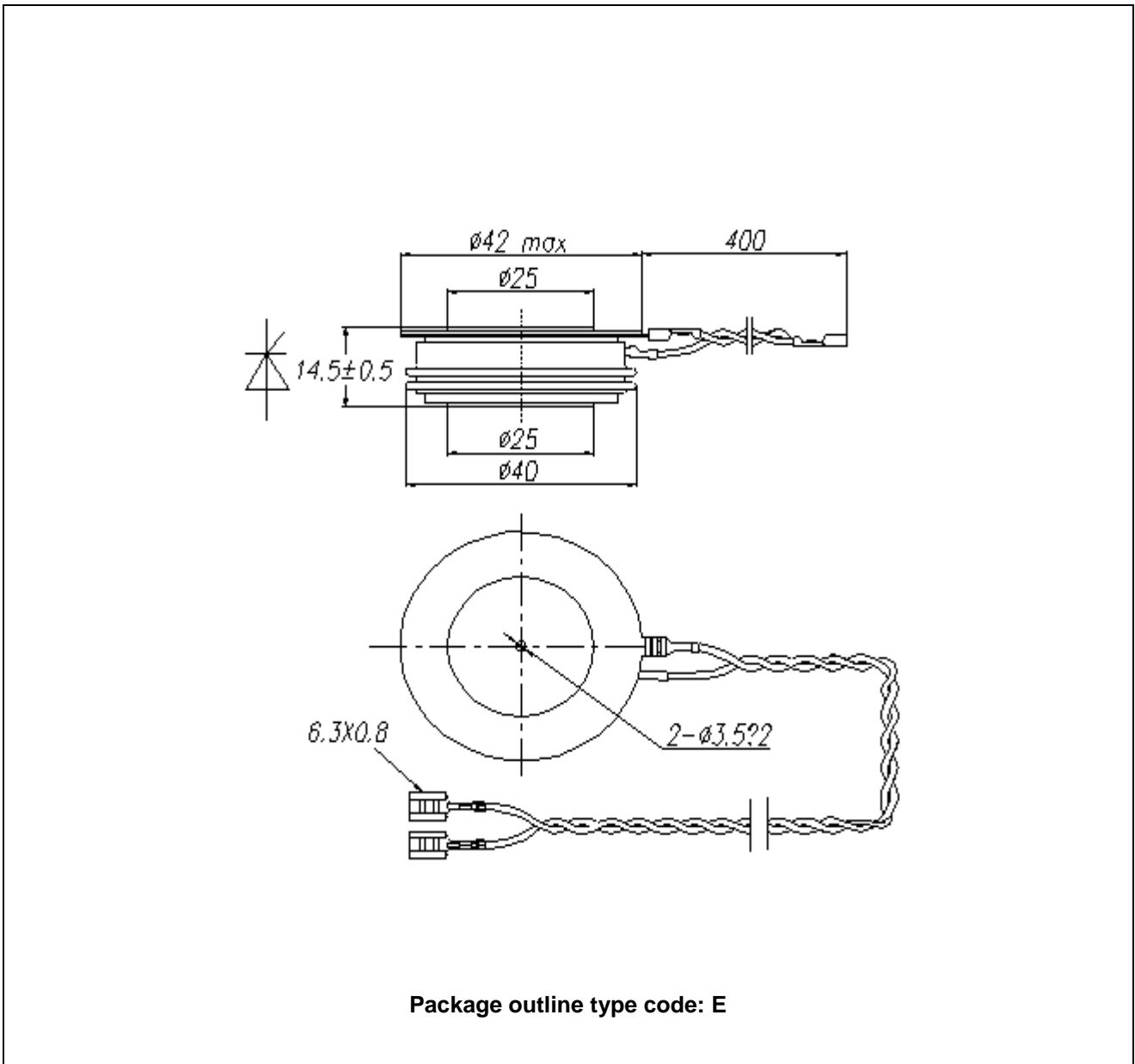


Fig. 14 Package outline

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